

RJK0348DSP

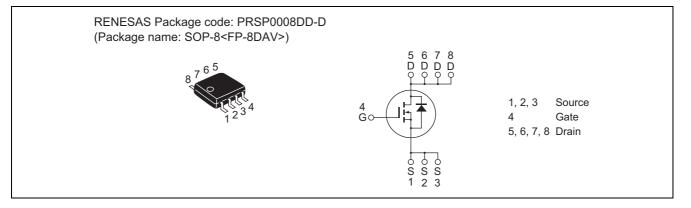
Silicon N Channel Power MOS FET Power Switching

> REJ03G1644-0201 Rev.2.01 Apr 24, 2008

Features

- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
- $R_{DS(on)} = 2.6 \text{ m}\Omega \text{ typ.}$ (at $V_{GS} = 10 \text{ V}$)
- Pb-free

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	22	A
Drain peak current	Note1 I _{D(pulse)}	176	A
Body-drain diode reverse drain current	I _{DR}	22	A
Avalanche current	I _{AP} Note 2	22	A
Avalanche energy	E _{AR} Note 2	48.4	mJ
Channel dissipation	Pch Note3	2.5	W
Channel to ambient thermal impedance	θch-a ^{Note3}	50	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	۵°

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

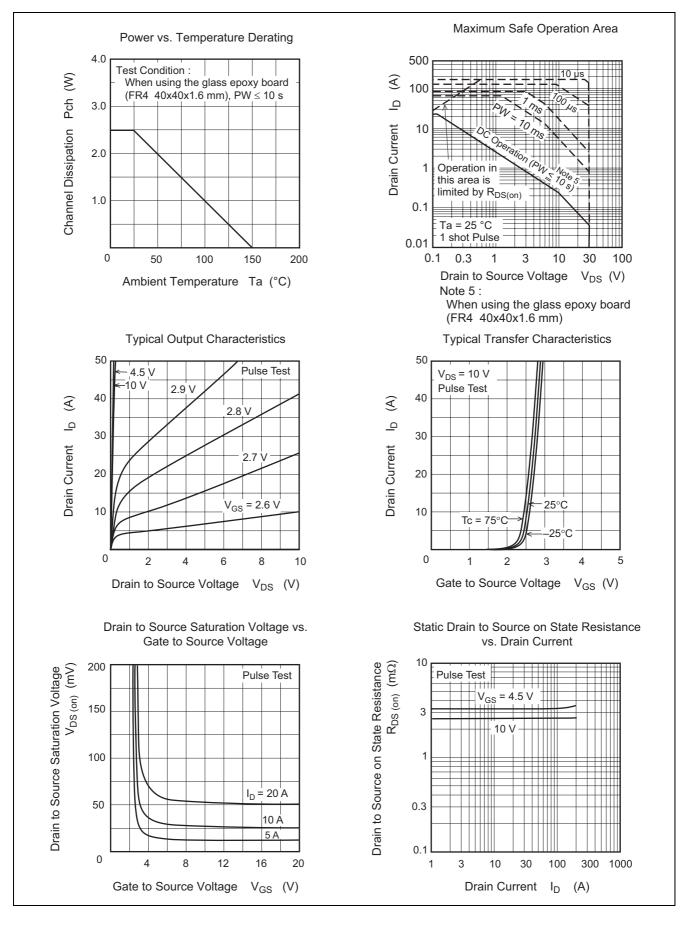
- 2. Value at Tch = 25°C, Rg \geq 50 Ω
- 3. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10s

Electrical Characteristics

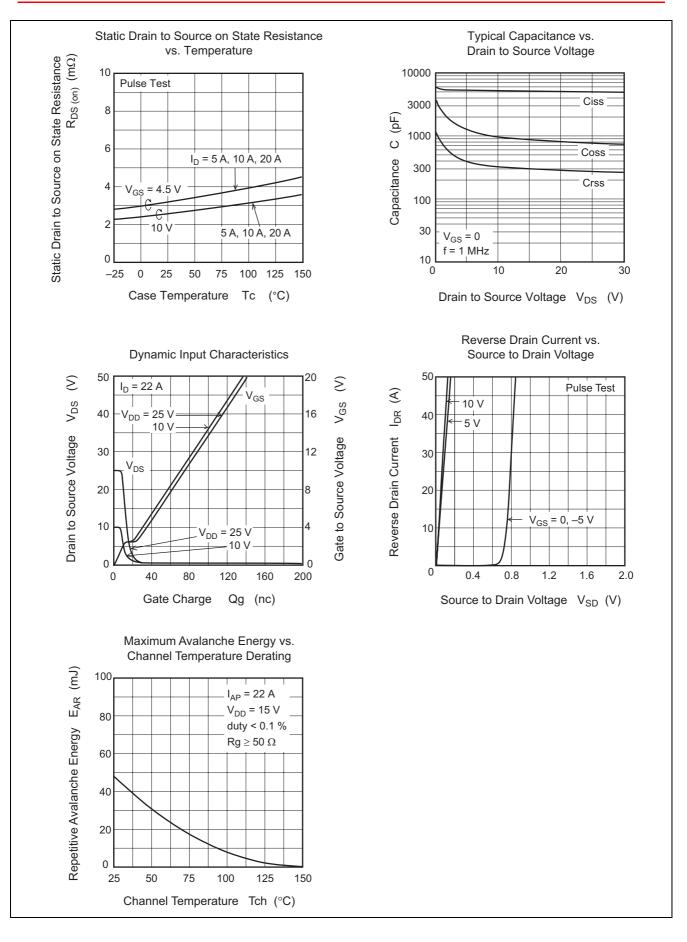
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	30	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}		—	± 0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, \text{ V}_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 30 V, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	1.2	—	2.5	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	2.6	3.4	mΩ	$I_D = 11 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance	R _{DS(on)}	_	3.2	4.5	mΩ	$I_D = 11 \text{ A}, V_{GS} = 4.5 \text{ V}^{Note4}$
Forward transfer admittance	y _{fs}	_	60	—	S	$I_D = 11 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss		5100	_	pF	V _{DS} = 10 V
Output capacitance	Coss		980	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss		315	_	pF	
Gate Resistance	Rg		1.4	_	Ω	
Total gate charge	Qg		34	_	nC	$V_{DD} = 10 V$ $V_{GS} = 4.5 V$ $I_D = 22 A$
Gate to source charge	Qgs	_	12.5	_	nC	
Gate to drain charge	Qgd		7.0	—	nC	
Turn-on delay time	t _{d(on)}		13	—	ns	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 11 \text{ A}$
Rise time	tr		5.8	—	ns	$V_{DD} \cong 10 \text{ V}$ $R_{L} = 0.91 \Omega$ $Rg = 4.7 \Omega$
Turn-off delay time	t _{d(off)}		69	—	ns	
Fall time	t _f	_	10	_	ns	
Body–drain diode forward voltage	V_{DF}	_	0.78	1.02	V	$I_F = 22 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body–drain diode reverse recovery	t _{rr}		35	—	ns	$I_F = 22 \text{ A}, V_{GS} = 0$
time						$di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 4. Pulse test

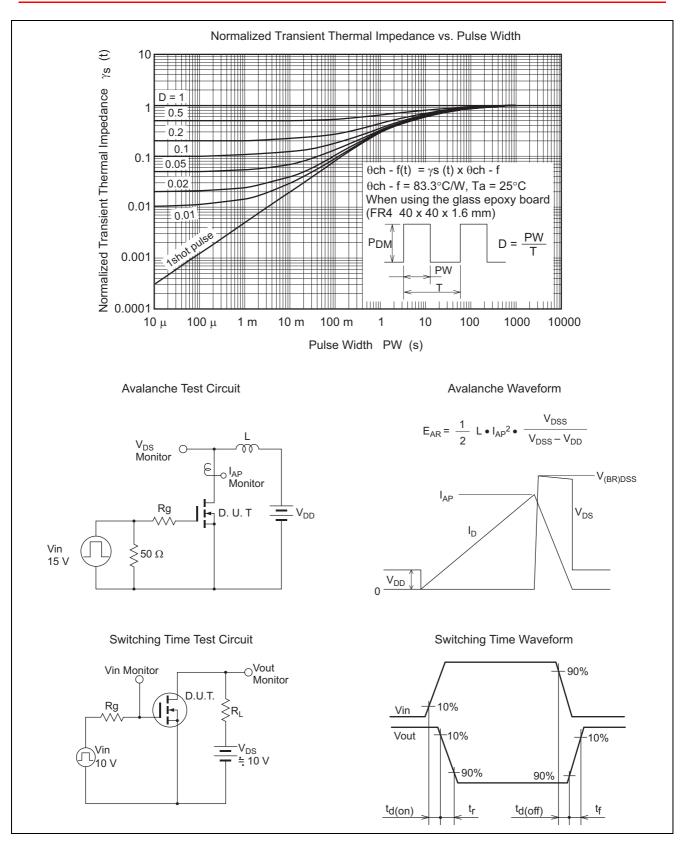
Main Characteristics



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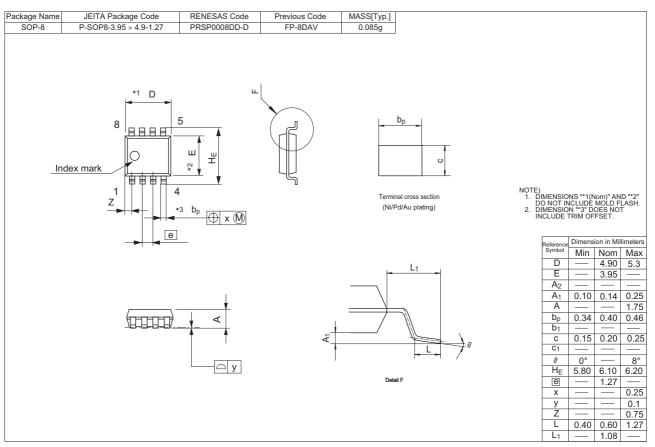


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Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK0348DSP-00-J0	2500 pcs	Taping

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